

This device is designed for use in low noise UHF/VHF amplifiers with collector currents in the 100 μ A to 30 mA range in common emitter or common base mode of operation, and in low frequency drift, high ouput UHF oscillators. Sourced from Process 40.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	12	V
V _{CBO}	Collector-Base Voltage	20	V
V _{EBO}	Emitter-Base Voltage	2.5	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

<u>NOTES</u>: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		PN/MPS5179	*MMBT5179	
PD	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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NPN RF Transistor

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	12		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 1.0 \ \mu A, \ I_{\rm E} = 0$	20		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	2.5		V
СВО	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$ $V_{CB} = 15 \text{ V}, \text{ T}_{A} = 150^{\circ}\text{C}$		0.02 1.0	μΑ μΑ
	ACTERISTICS	I _C = 3.0 mA, V _{CE} = 1.0 V	25	250	
/ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.4	V
	Base-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		1.0	V

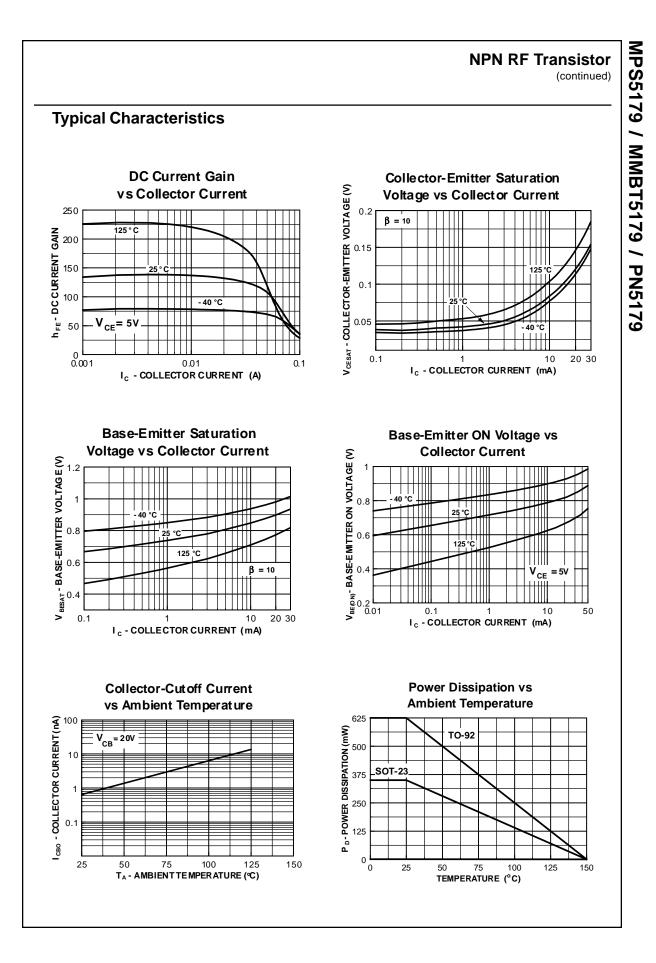
f _T	Current Gain - Bandwidth Product	$I_{C} = 5.0 \text{ mA}, V_{CE} = 6.0 \text{ V},$ f = 100 MHz	900	2000	MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0,$ f = 0.1 to 1.0 MHz		1.0	pF
h _{fe}	Small-Signal Current Gain	$I_{C} = 2.0 \text{ mA}, V_{CE} = 6.0 \text{ V},$ f = 1.0 kHz	25	300	
rb'C _c	Collector Base Time Constant	$I_{C} = 2.0 \text{ mA}, V_{CB} = 6.0 \text{ V},$ f = 31.9 MHz	3.0	14	ps
NF	Noise Figure	$I_{C} = 1.5 \text{ mA}, V_{CE} = 6.0 \text{ V},$ $R_{S} = 50\Omega, \text{ f} = 200 \text{ MHz}$		5.0	dB

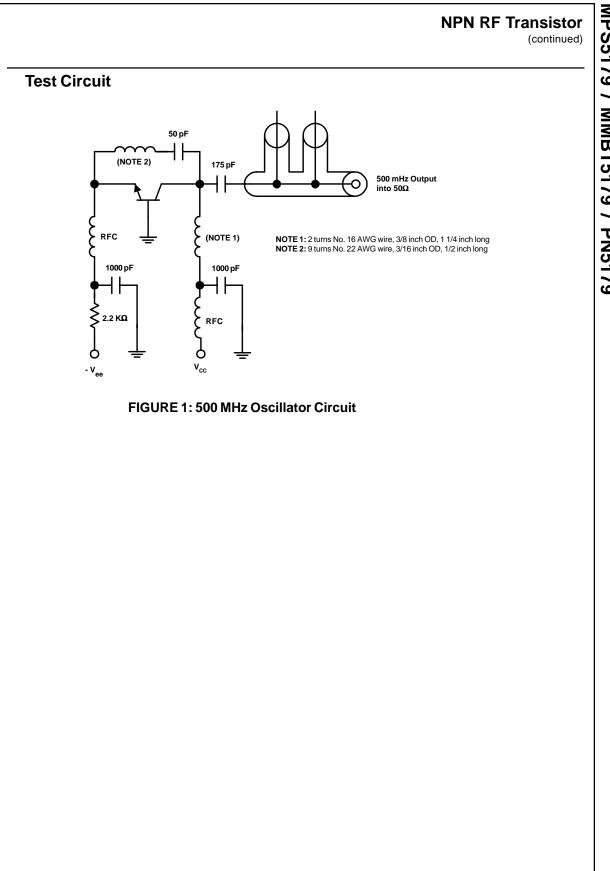
FUNCTIONAL TEST

G _{pe}	Amplifier Power Gain	$V_{CE} = 6.0 \text{ V}, I_{C} = 5.0 \text{ mA},$ f = 200 MHz	15	dB
Po	Power Output	$\label{eq:V_CB} \begin{array}{l} V_{CB} = 10 \ V, \ I_E = 12 \ mA, \\ f \geq 500 \ MHz \end{array}$	20	mW

*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Spice Model





MPS5179 / MMBT5179 / PN5179



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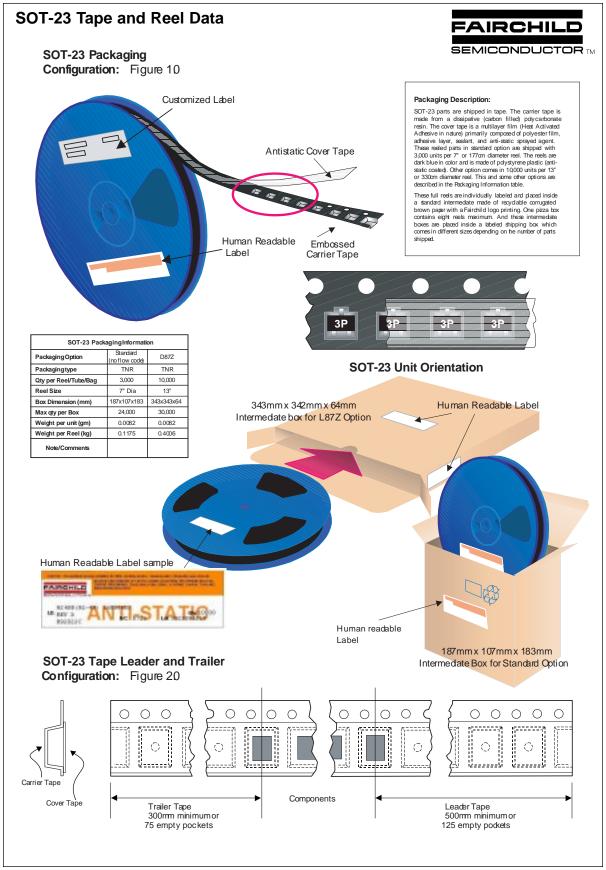
March 2001, Rev. B1





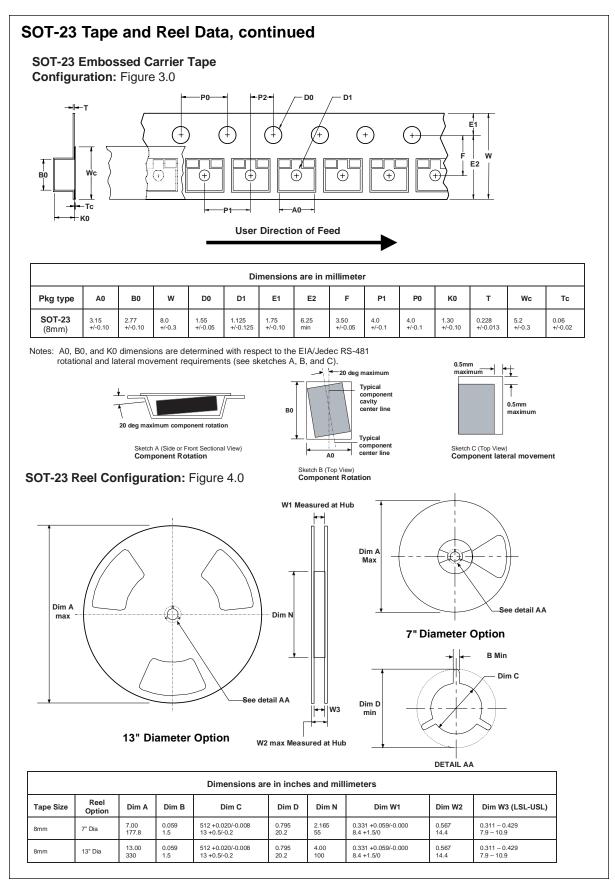
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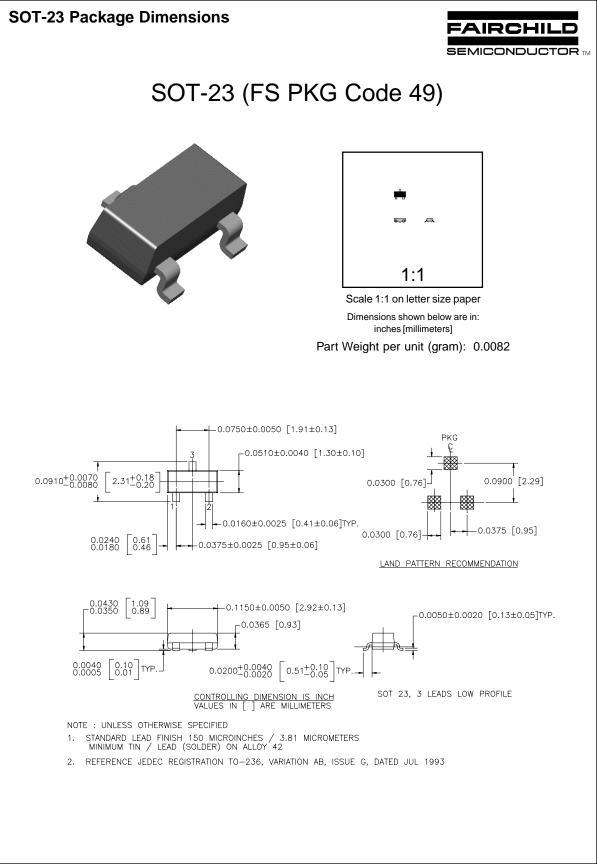


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